TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

HN3C01F

TV TUNER, VHF CONVERTER APPLICATION. TV VHF RF AMPLIFIER APPLICATION.

Including Two Devices in SM6 (Super Mini Type with 6Leads)

Low Reverse Transfer Capacitance : $C_{re} = 0.38pF$ (Typ.) High Transition Frequency : $f_T = 1400 MHz (Typ.)$

MAXIMUM RATINGS (Ta = 25° C) (Q₁, Q₂)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	VCEO	20	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	$I_{\mathbf{C}}$	50	mA
Base Current	I _B	25	mA
Collector Power Dissipation	PC*	300	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	$ m T_{stg}$	-55~125	°C

Total ELECTRICAL CHARACTERISTICS (Ta = 25°C) (Q₁, Q₂)

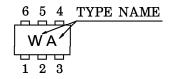
		Unit in m	m
		+0.2 2.8-0.3 1.6-0.1 6 T0 15 E8	•
	11.1-0.12	016-0.06	1
1.	COLLECTOR 1	(C1) 5	
2.	COLLECTOR 1 EMITTER 1	(E1) ?	
3.	COLLECTOR 2	(C2)	
4.	EMITTER 2	(E2)	
5.	BASE 2	(B2)	
6.	BASE 1	(B1)	
JΕ	DEC	_	
\mathbf{EL}	AJ	_	
ТО	SHIBA 2	2-3N1B	

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 25V, I_{E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	IEBO	$V_{EB}=3V, I_{C}=0$	_	_	1.0	μ A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_{\rm C}=1{ m mA},~I_{\rm B}=0$	20	_	_	V
DC Current Gain	$h_{ ext{FE}}$	$V_{CE}=10V, I_{C}=5mA$	40	150	300	_
Transition Frequency	$ m f_{T}$	$V_{\text{CE}} = 10\text{V}, I_{\text{C}} = 5\text{mA},$ f = 200MHz	900	1400	_	MHz
Reverse Transfer Capacitance Q ₁	C _{re (1)}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	_	0.38	0.53	рF
Reverse Transfer Capacitance Q2	C _{re (2)}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	0.31	0.46	рF
Collector-Base Time Constant Q1	Cc·rbb'(1)	V_{CB} =10V, I_{C} =5mA, f =30MHz	_	6.0	12	ps
Collector-Base Time Constant Q2	C _c ·r _{bb} ·(2)	V_{CB} =10V, I_{C} =5mA, f =30MHz	_	5.5	11.5	ps

PIN ASSIGNMENT (TOP VIEW)

MARKING





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